



(12) **United States Patent**
Schroeder et al.

(10) **Patent No.:** **US 9,448,278 B2**
(45) **Date of Patent:** **Sep. 20, 2016**

(54) **DIRECT LIQUID-CONTACT
MICRO-CHANNEL HEAT TRANSFER
DEVICES, METHODS OF TEMPERATURE
CONTROL FOR SEMICONDUCTIVE
DEVICES, AND PROCESSES OF FORMING
SAME**

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(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
U.S.C. 154(b) by 0 days.

(21) Appl. No.: **14/746,764**

(22) Filed: **Jun. 22, 2015**

(65) **Prior Publication Data**

US 2015/0285857 A1 Oct. 8, 2015

Related U.S. Application Data

(62) Division of application No. 12/590,379, filed on Nov.
6, 2009.

(51) **Int. Cl.**
G01R 31/28 (2006.01)
G01R 31/26 (2014.01)
(Continued)

(52) **U.S. Cl.**
CPC **G01R 31/2875** (2013.01); **G01R 31/2642**
(2013.01); **G06F 1/20** (2013.01);
(Continued)

(58) **Field of Classification Search**

CPC H01L 23/467; H01L 23/473
USPC 361/688, 689, 699; 324/765, 629
See application file for complete search history.

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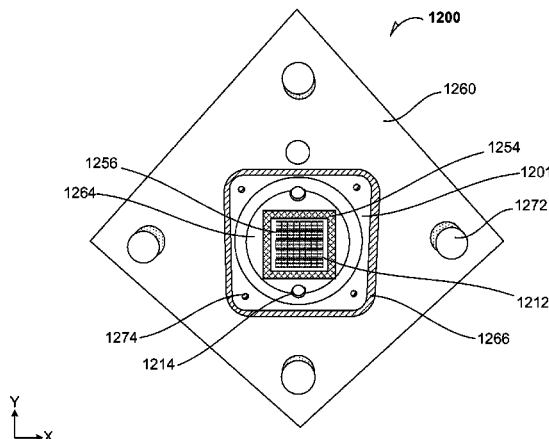
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(57) **ABSTRACT**

An apparatus to test a semiconductive device includes a base
plane that holds at least one heat-transfer fluid unit cell. The
at least one heat-transfer fluid unit cell includes a fluid
supply structure including a supply-orifice cross section as
well as a fluid return structure including a return-orifice
cross section. The supply-orifice cross section is greater than
the return-orifice cross section. A die interface is also
included to be a liquid-impermeable material.

18 Claims, 10 Drawing Sheets



- (51) **Int. Cl.**
G06F 1/20 (2006.01)
H01L 23/473 (2006.01)
H01L 23/467 (2006.01)
F28F 3/12 (2006.01)
- (52) **U.S. Cl.**
 CPC *F28F 3/12* (2013.01); *G06F 2200/201*
 (2013.01); *H01L 23/467* (2013.01); *H01L*
23/473 (2013.01); *H01L 2924/0002* (2013.01)

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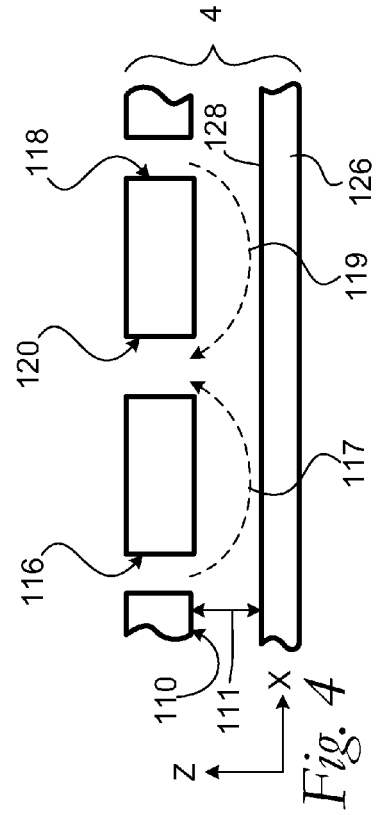
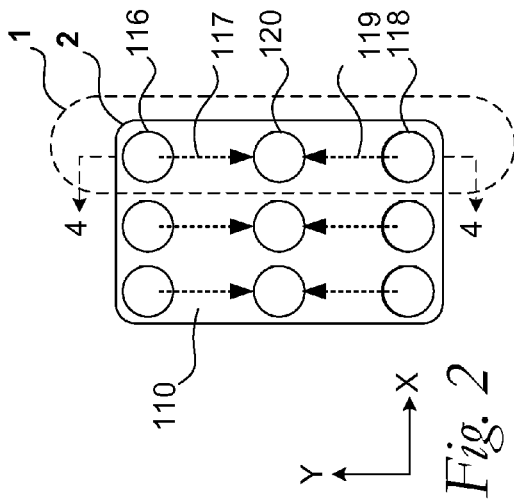
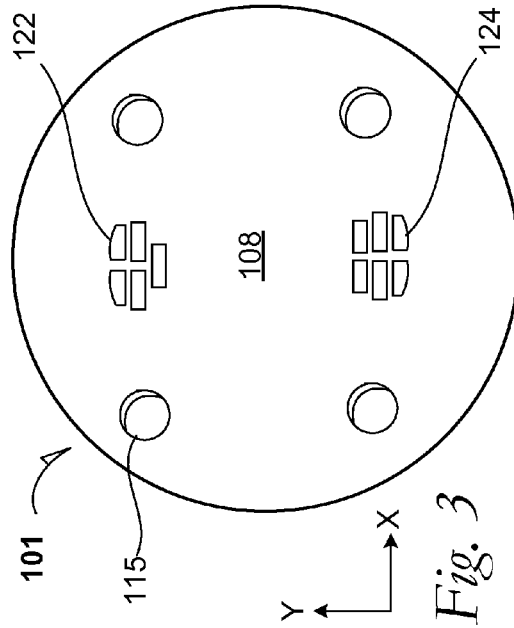
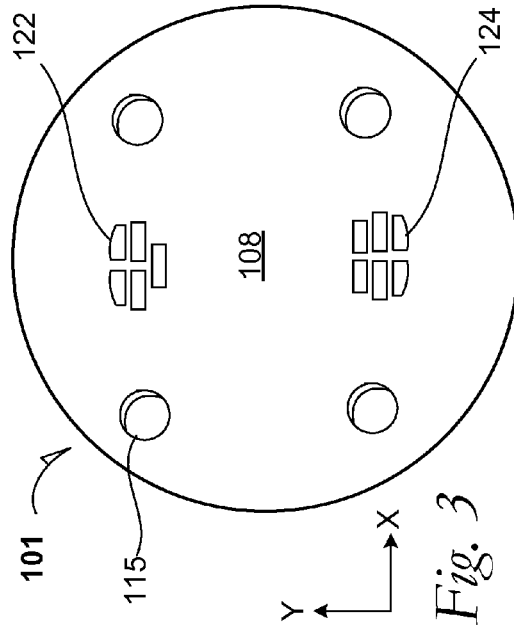
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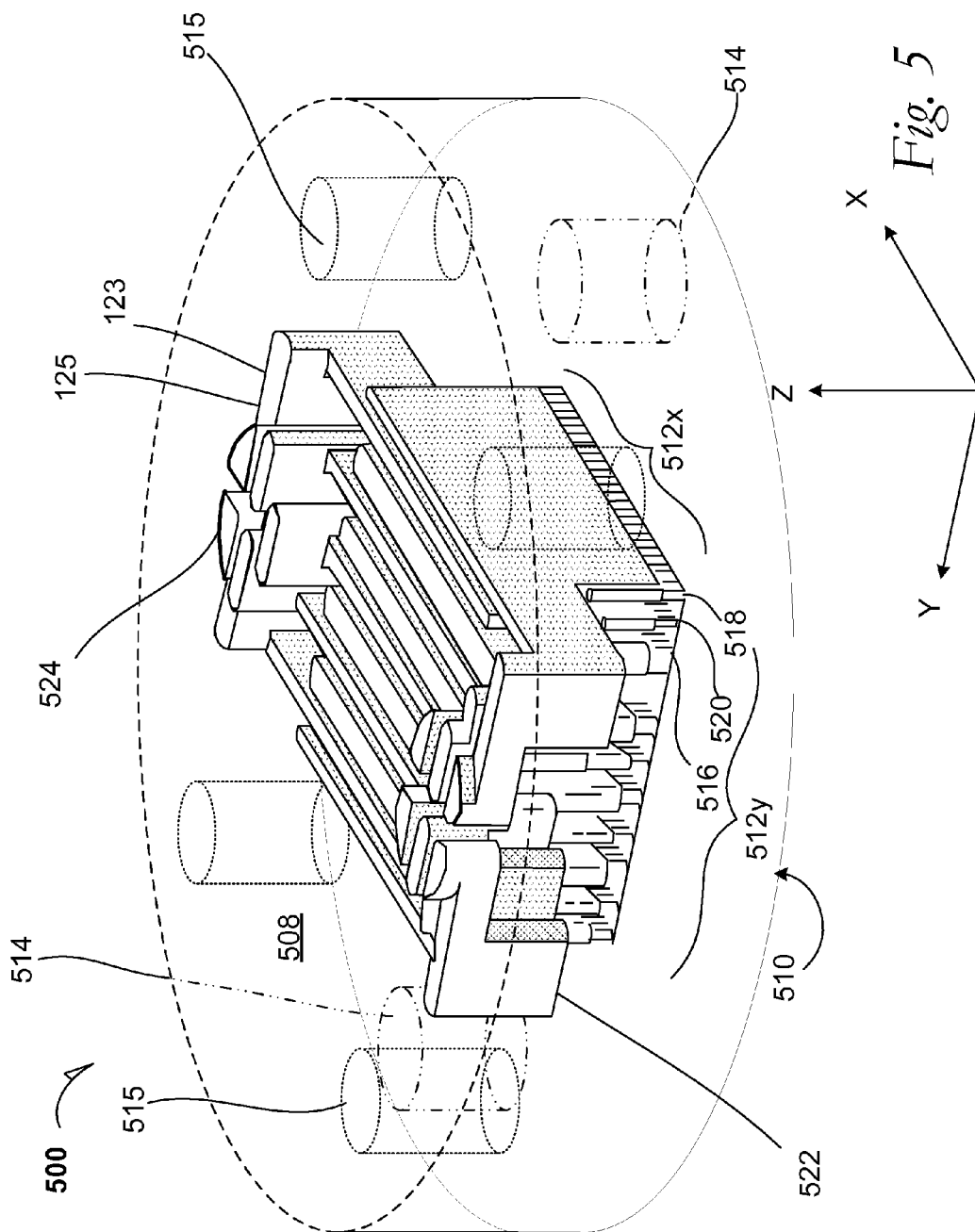
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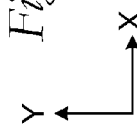
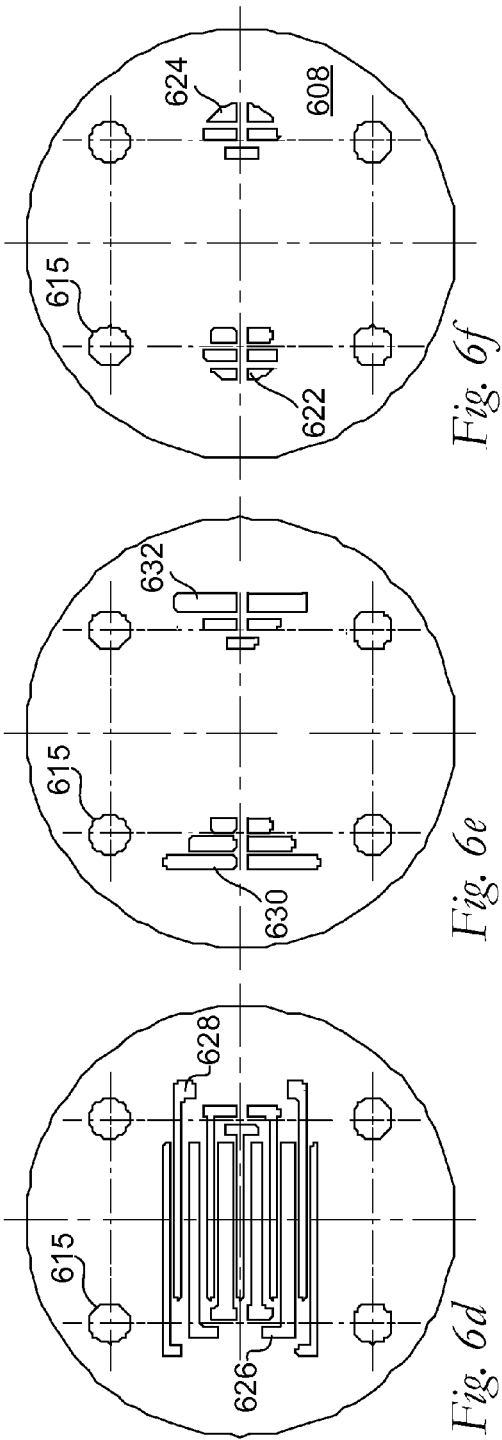
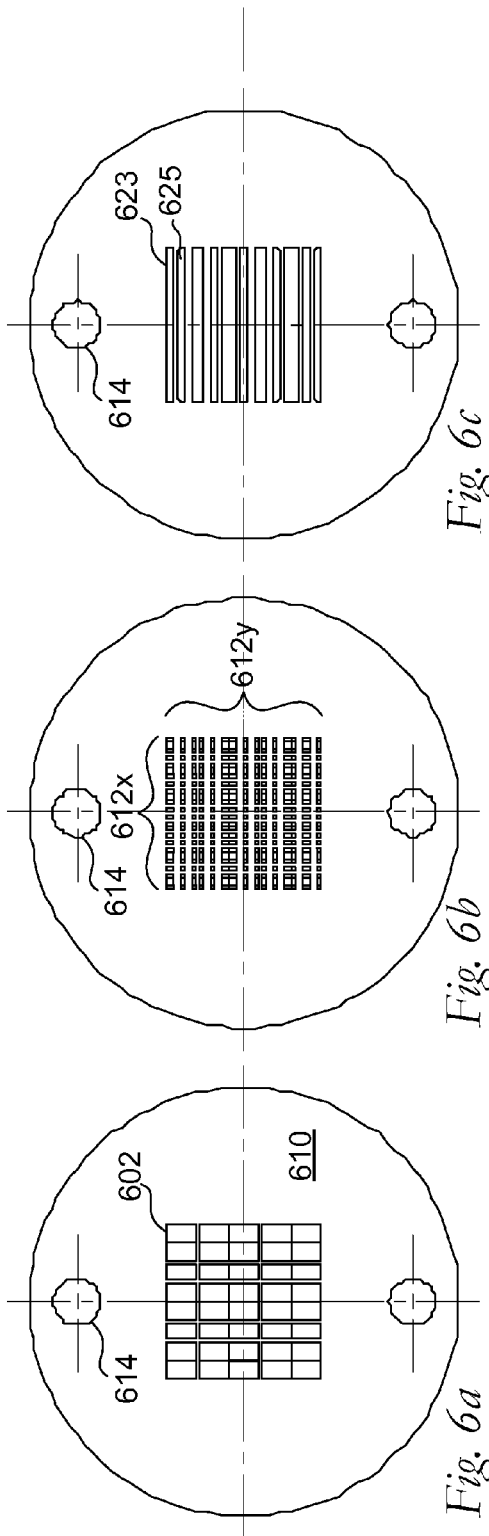


Fig. 7

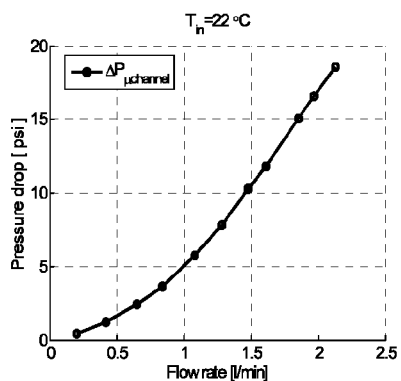


Fig. 8

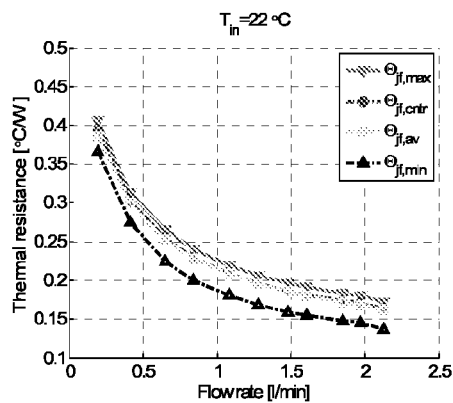
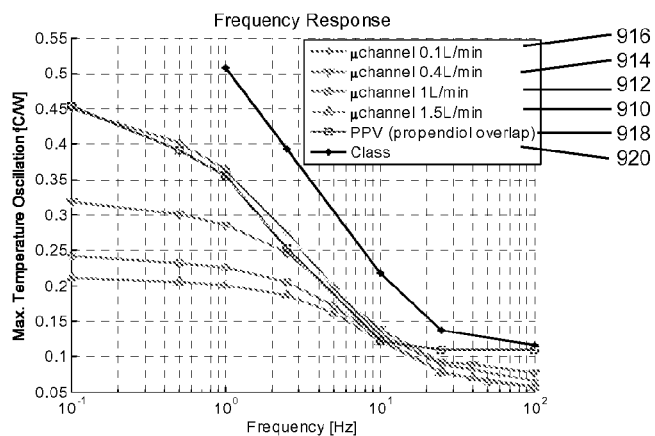
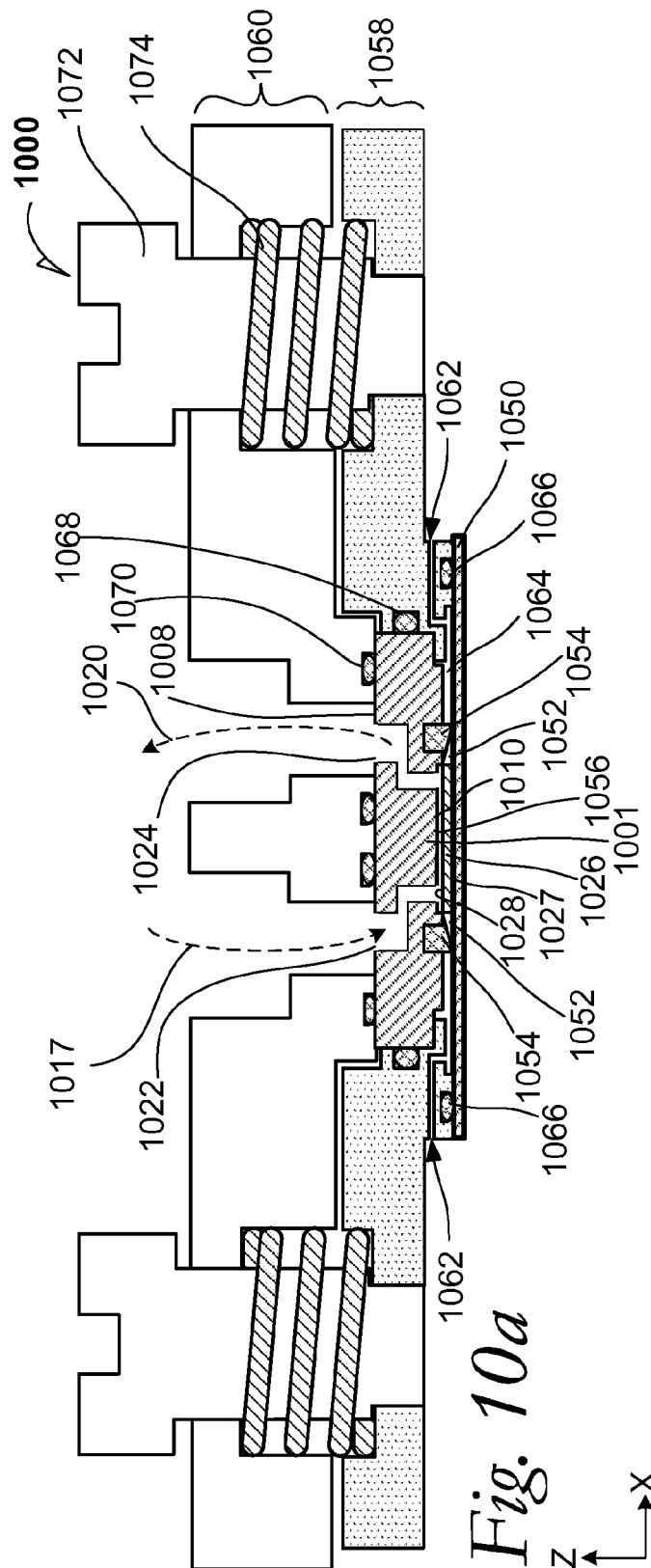
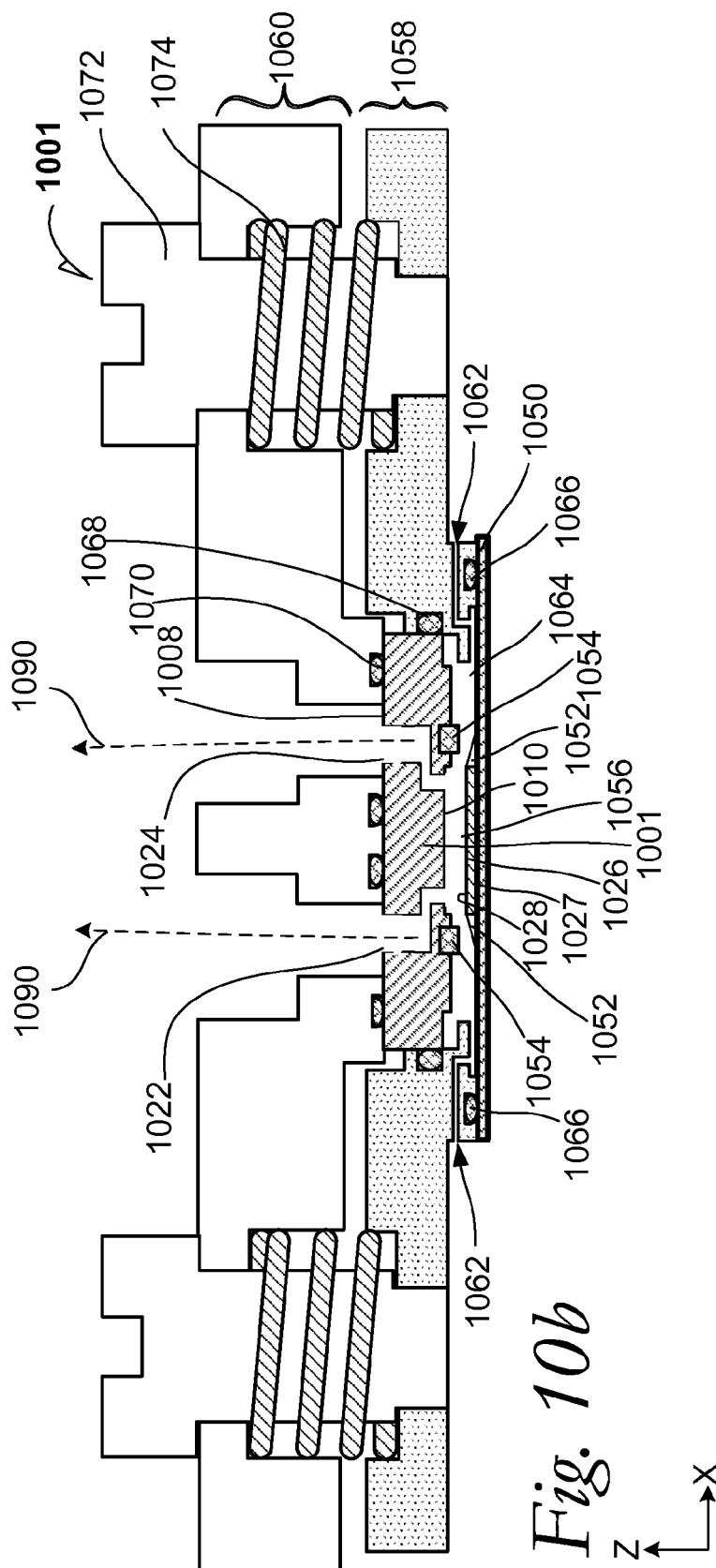


Fig. 9







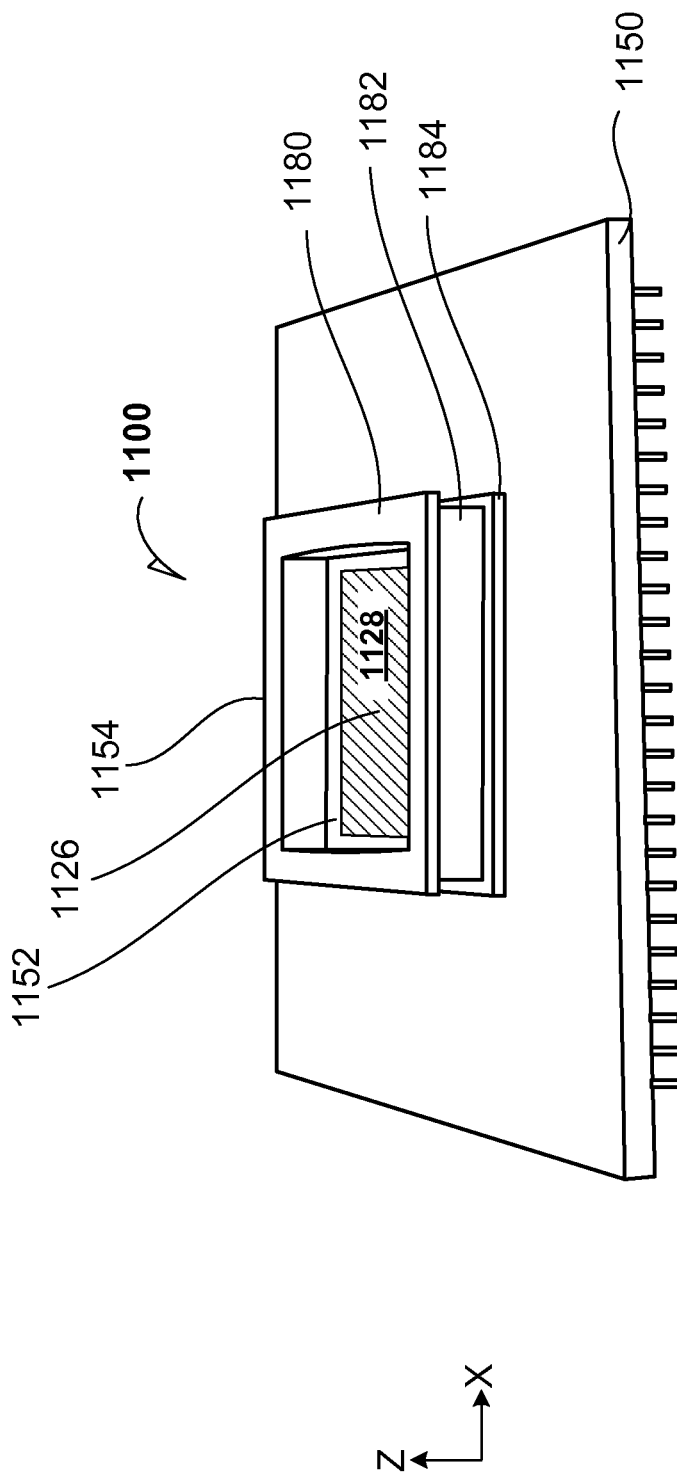
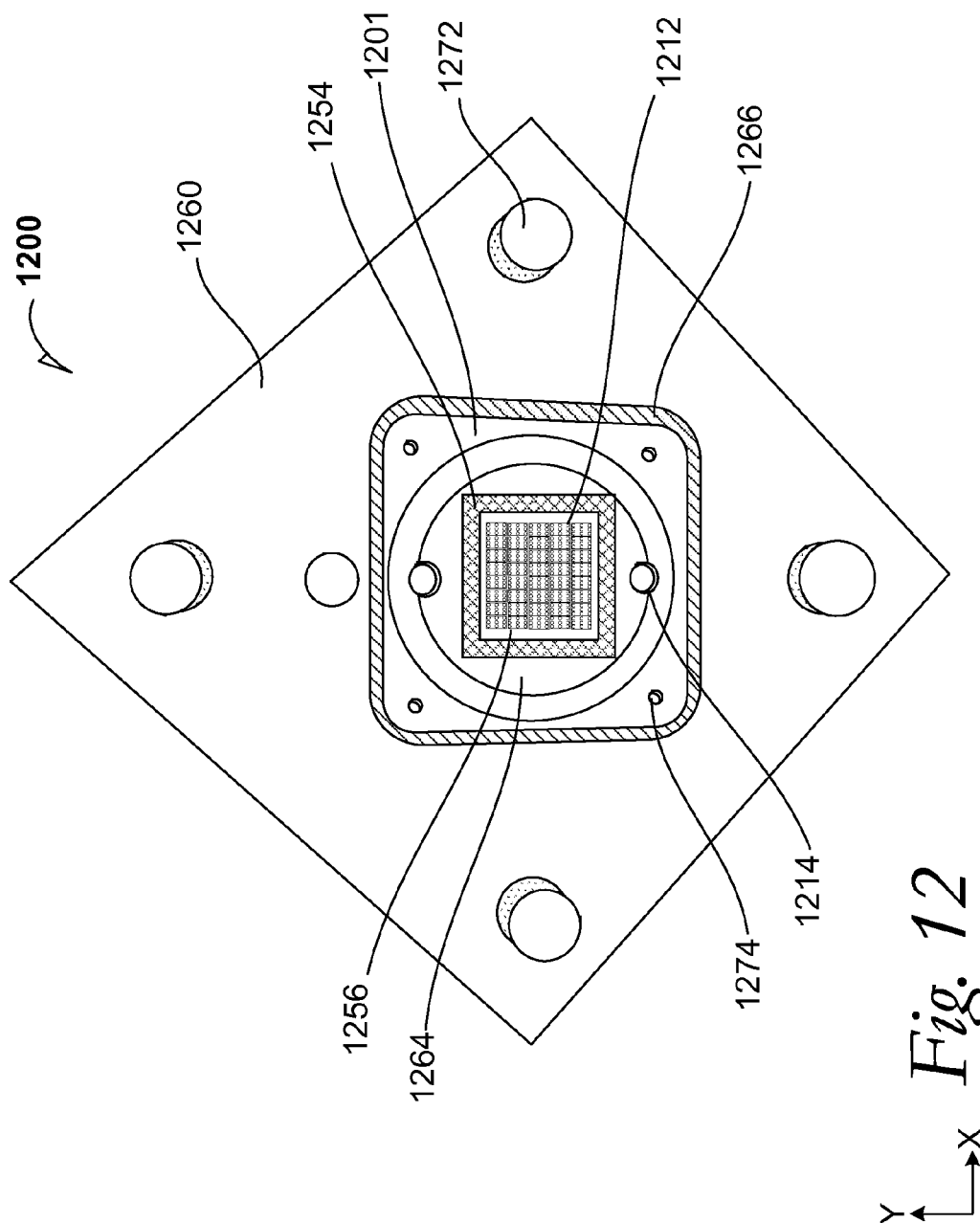


Fig. 11



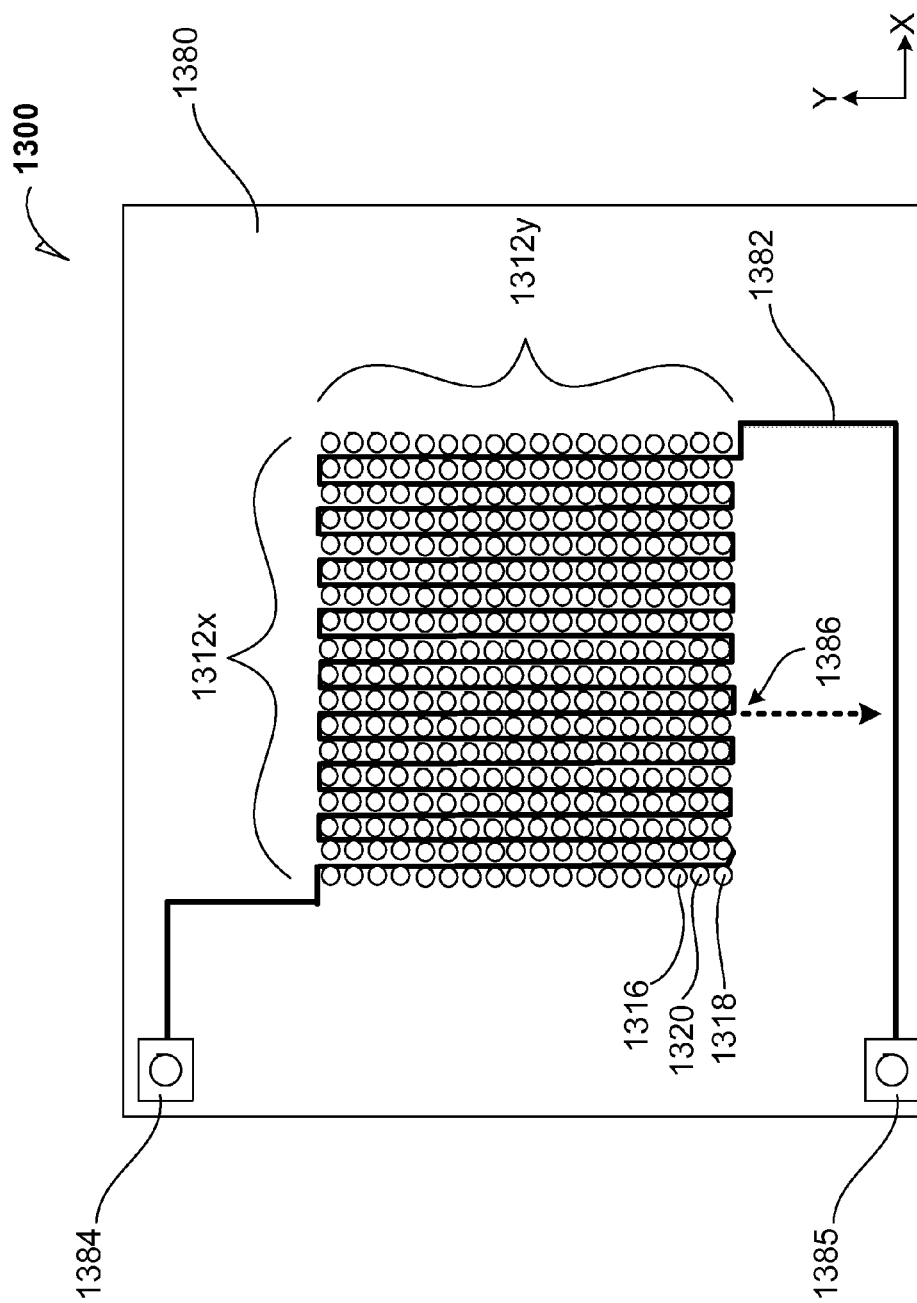


Fig. 13

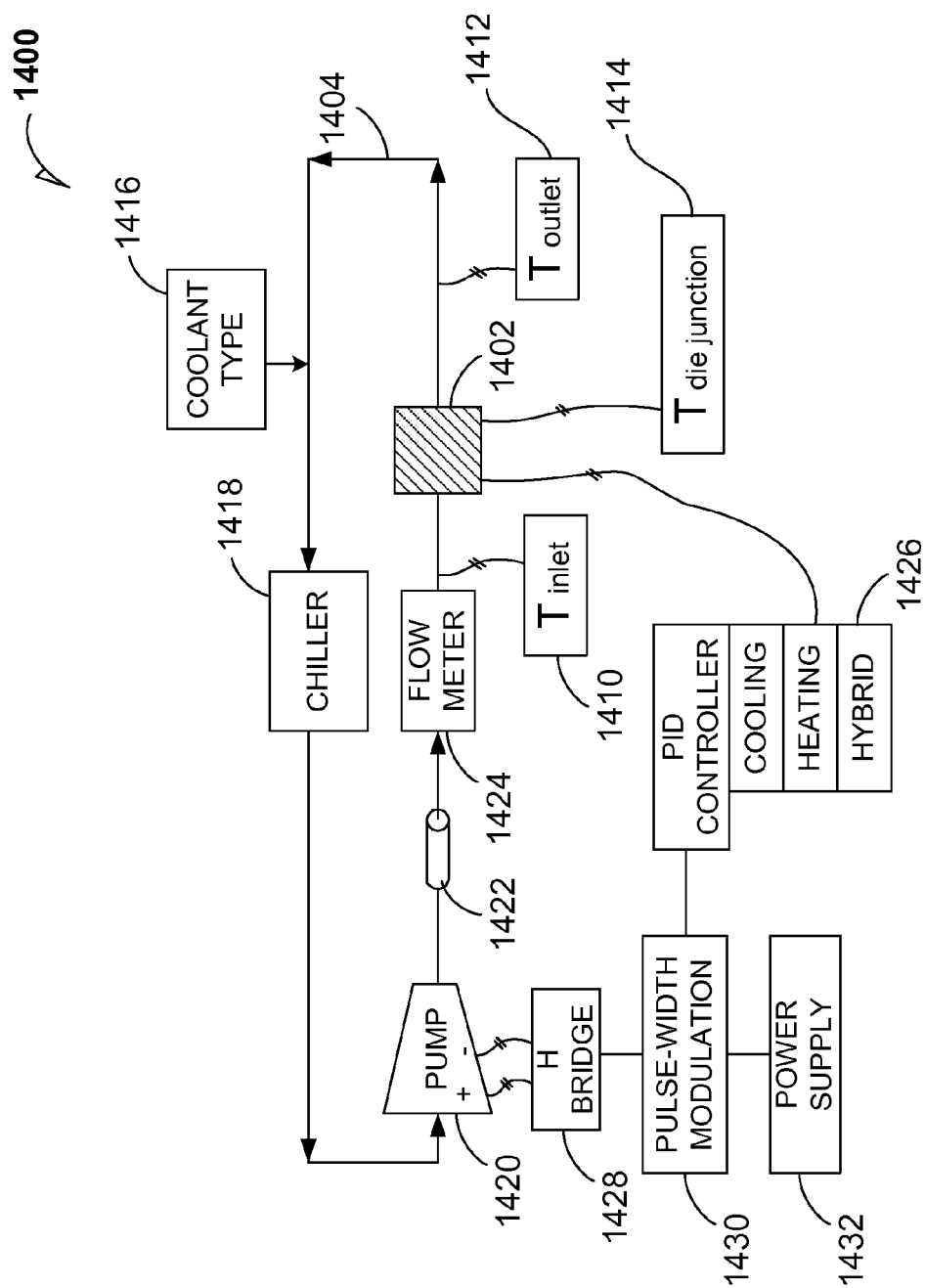


Fig. 14

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**DIRECT LIQUID-CONTACT
MICRO-CHANNEL HEAT TRANSFER
DEVICES, METHODS OF TEMPERATURE
CONTROL FOR SEMICONDUCTIVE
DEVICES, AND PROCESSES OF FORMING
SAME**

This application is a divisional of U.S. patent application Ser. No. 12/590,379 filed Nov. 6, 2009, which is hereby incorporated by reference in its entirety.

TECHNICAL FIELD

Microelectronic devices are put under severe workloads during use that may affect performance. Challenges involved with such devices include test performance as miniaturization continues to track Moore's Law.

BRIEF DESCRIPTION OF THE DRAWINGS

In order to understand the manner in which embodiments are obtained, a more particular description of various embodiments briefly described above will be rendered by reference to the appended drawings. These drawings depict embodiments that are not necessarily drawn to scale and are not to be considered to be limiting in scope. Some embodiments will be described and explained with additional specificity and detail through the use of the accompanying drawings in which:

FIG. 1 is a bottom plan of a direct fluid-contact thermal block for a semiconductive device cooling apparatus according to an embodiment;

FIG. 2 is a detail section of the indicated unit cell taken from the fluid-flow array depicted in FIG. 1 according to an example embodiment;

FIG. 3 is a top plan of the direct fluid-contact thermal block depicted in FIG. 1 according to an embodiment;

FIG. 4 is a cross-section detail that includes the unit cell depicted in FIG. 2 and taken along the section line 4-4 according to an embodiment;

FIG. 5 is a partially transparent perspective elevation of a direct fluid-contact thermal block according to an example embodiment;

FIGS. 6a through 6f illustrate several laminate layer types that make up a direct fluid-contact thermal block embodiment;

FIG. 7 is a graph that illustrates flow rate versus pumping pressure for a direct fluid-contact thermal block according to an example embodiment;

FIG. 8 is a graph of thermal performance in the flow range described in FIG. 7 according to several embodiments;

FIG. 9 is a graph of dynamic thermal response compared to a baseline according to several embodiments;

FIG. 10a is a cross-section elevation of a chip-testing system according to an example embodiment;

FIG. 10b is a cross-section elevation of the chip-testing system depicted in FIG. 10a after further processing according to an embodiment;

FIG. 11 is a perspective elevation of a portion of a chip-testing system 1100 according to an example embodiment;

FIG. 12 is a bottom perspective plan of a chip-testing system 1200 according to an example embodiment;

FIG. 13 is a top plan of a resistive heater that is embedded in a laminate layer for a fluid-contact thermal block according to an example embodiment; and

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FIG. 14 is a control method diagram according to several embodiments.

DETAILED DESCRIPTION

Reference will now be made to the drawings wherein like structures may be provided with like suffix reference designations. In order to show the structures of various embodiments more clearly, the drawings included herein are diagrammatic representations of integrated circuit structures. Thus, the actual appearance of the fabricated integrated circuit structures, for example in a photomicrograph, may appear different while still incorporating the claimed structures of the illustrated embodiments. Moreover, the drawings may only show the structures useful to understand the illustrated embodiments. Additional structures known in the art may not have been included to maintain the clarity of the drawings.

FIG. 1 is a bottom plan of a direct fluid-contact thermal block 100 for a semiconductive device cooling apparatus according to an embodiment. A die interface surface 110 exhibits a fluid-flow array 112 with a plurality of unit cells, one of which is indicated with the reference numeral 1. The fluid-flow array 112 may also be referred to as a device-under-test (DUT) footprint 112 and is configured to approximately match a device such as a processor die.

In the illustrated embodiment, the fluid-flow array 112 includes 120 unit cells defined by a 24 unit-cell dimension 112x along an X-axis and a five unit-cell dimension 112y along a Y-axis. The die interface surface 110 is part of a base plane of a plurality of stacked composites that form the direct fluid-contact thermal block 100 according to an embodiment. A plurality of head bolt orifices are provided, one of which is indicated with reference numeral 114.

FIG. 2 is a detail section of the indicated unit cell 1 taken from the fluid-flow array 112 depicted in FIG. 1 according to an example embodiment. The unit cell 1 is grouped with two other unit cells within a unit block 2 embodiment. The unit block 2 embodiment encompasses the die interface surface 110 and in this embodiment includes nine orifices for fluid flow. As seen in FIG. 1, the unit cells are grouped in threes within the unit block 2 embodiment (FIG. 2), and the unit block 2 embodiments are grouped as an eight-by-five unit block array of micro-scale channels.

The unit block 2 embodiment includes a fluid-supply structure with six orifices and a fluid-return structure with three orifices. The unit cell 1 is configured such that there is a larger cross sectional area for the total of fluid-supply-orifice(s) than for the total of fluid-return-orifice(s). As illustrated, the comparative larger fluid-supply-orifice cross section (hereinafter fluid-supply orifice) is embodied by a fluid-supply first orifice 116 and a fluid-supply subsequent orifice 118, and it is compared to a single fluid-return orifice 120. Fluid flow direction is illustrated with arrows 117 and 119.

FIG. 3 is a top plan of the direct fluid-contact thermal block 101 depicted in FIG. 1 according to an embodiment. The direct fluid-contact thermal block 101 shows a top plane 108 that is depicted as the top surface of the thermal block 101. Supply-fluid inlets 122 and return-fluid outlets 124 are also depicted. The supply- and return-fluid inlets and outlets 122 and 124, respectively, are coupled through distribution channels to unit cells that are located on the bottom at the die interface surface 110 (FIG. 1).

A plurality of head bolt orifices are provided, one of which is enumerated with reference 115. As described

below, supply and return channels are provided between the die interface surface **110** (or base plane **110**) and the top plane **108**.

FIG. **4** is a cross-section detail **4** that includes the unit cell **1** depicted in FIG. **2** and taken along the section line **4-4** according to an embodiment. A testing system **103** is depicted including the base plane **110** and a die **126** to be cooled or otherwise heat-controlled as a device-under-test (DUT **126**). The DUT **126** includes an active surface **127** and a backside surface **128**. In an embodiment, the DUT **126** is a flip chip.

The base plane **110** is presented facing the die **126**. In an embodiment, spacing **111** between the backside **128** of the die **126** and the base plane is in a range from 20 micrometer (μm) to 2 millimeter (mm). In an embodiment, spacing **111** is 75 μm . Other spacing lengths may be used depending upon a specific application. In an embodiment where the fluid-flow array **112** (FIG. **1**) is about 1 centimeter (cm) squared, spacing **111** is about 1 mm. In other embodiments, spacing is a range from 0.1 mm to 2 mm depending upon die size and an achieved heat-transfer flow regime that may be turbulent.

In an embodiment, the backside surface **128** is a bare die backside surface. In an embodiment, the die **126** has a metallization layer that constitutes the backside surface **128**. In either embodiment, the backside surface **128** may be referred to as "bare die" with respect to temperature-control fluid making direct-fluid contact at the backside surface **128**.

In the unit cell **1**, fluid flow **117** is directed out of the fluid-supply first orifice **116** against the backside **128** of the die **126** for direct-fluid contact, followed by the fluid flow **117** of necessity exiting the single fluid-return orifice **120**. It can be seen that fluid flow **119** is also directed out of the fluid-supply subsequent orifice **118**, against the backside **128** of the die **126** for direct-fluid contact, followed by the fluid flow **119** of necessity also exiting the single fluid-return orifice **120**. As a consequence of the configuration of the unit cell **1** (FIG. **2**), the fluid-supply-orifice cross-section area is larger than the fluid-return-orifice cross section area.

In an embodiment, directing the fluid flow **117** and **119** is done onto the backside of the die and the fluid is a mixture of a liquid and a gas. In an embodiment, the fluid flow **117** and **119** is an expandable fluid such as a refrigerant such that two-phase flow is carried out. For example, the fluid flow **117** and **119** are liquid-phase flow, but at least a portion of the fluid flow **117** and **119** as they enter the fluid-return orifice **120** are vapor or gas-phase flow. Accordingly, latent heat of vaporization is transferred from the backside **128** of the die into the liquid-phase to cause the vapor- or gas phase to appear. Consequently, laminar liquid fluid flow is disrupted and driven toward turbulent flow by flashing of the coolant. Similarly, already turbulent liquid fluid flow is disrupted and driven toward more turbulent flow by flashing of the coolant.

Other embodiments may include the configuration where the fluid-supply-orifice cross-section area is larger than the fluid-return-orifice cross section area. In an example embodiment, the fluid-supply-orifice cross-section area is larger than the fluid-return-orifice cross section area by virtue of equal cross-section area orifices, but there are provided more supply orifices than return orifices. This may be seen in the specific embodiment depicted in FIGS. **2** and **4**. In an embodiment, the fluid-supply-orifice cross-section area is larger than the fluid-return-orifice cross section by virtue of larger supply orifices than return orifices. Other embodiments may be carried out to accomplish the fluid-

supply-orifice cross-section area to be larger than the fluid-return-orifice cross section area.

In an embodiment, flow is a bilateral perimeter-supply flow regime as illustrated in FIGS. **2** and **4**. The flow is an influx regime at two perimeters of the unit cell **1** and an exit-flow regime at the center of the unit cell **1**. It can now be observed that flow within a unit cell is primarily constrained by at least one adjacent fluid-flow unit cell. For example, even where the unit block **2** is a corner block in the fluid-flow array **112**, and the unit cell **1** is at the corner, because it is adjacent three unit cells, flow is primarily constrained by at least one adjacent fluid-flow unit cell. The unit cell to the left of unit cell **1** is constrained by 5 adjacent unit cells where the unit block **2** is along an edge of the fluid-flow array **112**. And the unit cell to the left of unit cell **1** is constrained by 8 adjacent unit cells where the unit block **2** is anywhere away from an edge of the fluid-flow array **112**.

It can be seen that the DUT **126** is not touched by any equipment of the direct fluid-contact thermal block. Consequently, the application of direct fluid microchannel cooling to DUTs is a useful method for minimizing test-transient temperature responses because the heat transfer fluid makes direct contact with the device while the heat transfer fluid is forced into a micro scale flow regime that may be turbulent or streamlined (also referred to as laminar). The test equipment itself does not make physical contact with the surface of the DUT into which or from which heat will be transferred. As a consequence of no physical contact during testing, manufacturing yield loss is reduced. Such yield loss may arise from cosmetic product damage when mechanical contact is made in a conventional manner, although physical damage may also be a source of manufacturing yield loss.

It can be seen from FIG. **4** that converging short loop channel flow without separation walls at the base plane **110** reduces stagnation zones on the backside surface **128** of the die **126** to improve heat transfer. This converging short loop channel flow without separation walls may result in greater temperature uniformity while improving manufacturability.

FIG. **5** is a partially transparent perspective elevation of a direct fluid-contact thermal block **500** according to an example embodiment. A top surface **508** and a base plane **510** represent the bounds in the Z-dimension for the direct fluid-contact thermal block **500**. Head bolt orifices **514** are represented to communicate through the base plane **510** but not to breach the top surface **508**. Four head bolt orifices **515** (two referenced) are represented to communicate through the top surface **508**, but not to breach the base plane **510**.

A unit cell is indicated with a fluid-supply first orifice **516** and a fluid-supply subsequent orifice **518**, along with a single fluid-return orifice **520**. Fluid flow direction is therefore a bilateral perimeter flow from the fluid-supply orifices **516** and **518** to the center at the fluid-return orifice **520** without the use of separation walls or baffles. The several unit cells are arranged in a fluid-flow array **512** that is defined by a dimension **512x** along an X-axis and a unit-cell dimension **512y** along a Y-axis.

Fluid supply to the direct fluid-contact thermal block **500** is facilitated with supply-fluid inlets **522**. As illustrated, six supply-fluid inlets **522** are provided. Fluid return from the direct fluid-contact thermal block **500** is facilitated with five return-fluid outlets **524**. The supply- and return-fluid inlets and outlets **522** and **524**, respectively are coupled through distribution channels to unit cells that are located on the bottom at the die interface surface **510**.

Fluid distribution to and from the several unit cells is achieved with fluid-supply distributors, one of which is

indicated with reference numeral **523**, and fluid-return collectors, one of which is indicated with reference numeral **525**.

FIGS. **6a** through **6f** illustrate several laminate layer types that make up a direct fluid-contact thermal block embodiment.

In FIG. **6a**, first laminate type includes a die interface surface **610**. The first laminate type **6a** exhibits a fluid-flow array with a plurality of unit cells that are further grouped as unit blocks, one of which is illustrated with reference numeral **602**. Three unit cells multiplied by 40 unit blocks amounts to a total of 120 unit cells for a microchannel array in the illustrated embodiment.

In an embodiment, the first laminate type **6a** is 5 mils (thousandths of an inch, also 127 μm) thick and is a single layer. The die interface surface **610** is part of a base plane of a plurality of stacked composites that form a direct fluid-contact thermal block according to an embodiment. A plurality of head bolt orifices are provided, one of which is indicated with reference numeral **614**.

In FIG. **6b**, a second laminate type includes a fluid-flow array **612** of 120 unit cells defined by a 24 unit-cell dimension **612x** along an X-axis and a five unit-cell dimension **612y** along a Y-axis. The unit cells are made of supply orifices and a smaller number of return orifices according to an embodiment. In any event, the total cross-sectional area of the supply orifices is larger than the total cross-sectional area of the return orifices. The second laminate type **6b** is 5 mils thick (127 μm) and includes a total of 4 layers according to this embodiment.

In FIG. **6c**, a third laminate type includes fluid-supply distributors, one of which is indicated with reference numeral **623**, and fluid-return collectors, one of which is indicated with reference numeral **625**. The third laminate type **6c** is 10 mils (254 μm) thick and includes a total of nine layers according to this embodiment. A plurality of head bolt orifices are provided, one of which is indicated with reference numeral **614**.

In FIG. **6d**, a fourth laminate type includes fluid supply- and return routers **626** and **628**, respectively, that couple to the respective fluid supply- and return distributors and collectors **623** and **625**. The fourth laminate type **6d** is 10 mils (254 μm) thick and includes a total of nine layers according to this embodiment.

In FIG. **6e**, a fifth laminate type includes fluid supply- and return plenums **630** and **632**, respectively, that couple to the respective fluid supply- and return routers **626** and **628**. The fifth laminate type **6e** is 10 mils (254 μm) thick and includes a total of five layers in this embodiment.

In FIG. **6f**, a sixth laminate type includes a top plane **608** and is the top surface of this direct fluid-contact thermal block embodiment. Supply-fluid inlets **622** and return-fluid outlets **624** are also depicted. The supply- and return-fluid inlets and outlets **622** and **624**, respectively, are coupled to the respective fluid supply- and return plenums **630** and **632**. Consequently, the supply- and return-fluid inlets **622** and outlets **624** are coupled through the several distribution channels to unit cells that are located on the bottom at the die interface surface **610**. In this embodiment, the sixth laminate type **6f** is 10 mils (254 μm) thick and includes a total of two layers.

The several laminate types may be made of various materials. In an embodiment, the several laminate types are made of stainless steel. In an embodiment, the several laminate types are made of ceramics. In an embodiment, the several laminate types are made of plastics. Where the coefficient of thermal conductivity is lower than ordinary

steel, temperature stability in the heat-transfer fluid is facilitated. In an embodiment, the materials of the several laminate types is made of a material that has a coefficient of thermal conductivity that is less than that of stainless steel.

Fabrication of the direct fluid-contact thermal block can be done by 3-dimensional design techniques such as using computational-flow dynamics software. The etch and bonding qualities of the selected materials may also be taken into consideration during fabrication. In an embodiment, green ceramic laminate types are partially cured, assembled as a complete block, and then fully cured such as by firing. In an embodiment, direct laser melting is used to build up the several laminate types. In an embodiment, thermoplastic laminates are assembled and glued under heated bonding techniques. Other techniques may be used according to a selected application.

FIG. **7** is a graph of flow rate versus pumping pressure for a direct fluid-contact thermal block according to an example embodiment. The example embodiment is used on a 1 cm-by-1 cm die under test with a volumetric flow range between 0.5 liters to 2 liters per minute.

FIG. **8** is a graph of thermal performance in the flow range described in FIG. **7**. The thermal performance data indicated is for water as the cooling fluid. Flow rates from maximum to minimum were used to obtain the data.

FIG. **9** is a graph of dynamic thermal response compared to a baseline. The bottom thermal response line **910** was obtained with water at 1.5 L/min. The adjacent thermal response line **912** was obtained with water at 1 L/min. The following adjacent thermal response line **914** was obtained with water at 0.4 L/min. The following adjacent thermal response line **916** was obtained with water at 0.1 L/min. The following adjacent thermal response line **918** was obtained with propendiol. And the following adjacent thermal response line **920** was obtained using conventional techniques. In an embodiment, cooling response was improved by a factor of 2- to 5 times faster than over a conventional solution. As a consequence, the thermal analog to the resistance-capacitance (RC) response was improved between 200% and 500%.

FIG. **10a** is a cross-section elevation of a chip-testing system **1000** according to an example embodiment. A device under test **1026** (hereinafter DUT **1026**) is depicted with an active surface **1027** and a backside surface **1028**. The DUT **1026** may also be referred to as a die or as a semiconductor device. In an embodiment, the DUT **1026** is a processor such as an i3®, i5®, or i7® series processor made by Intel Corporation of Santa Clara, Calif. In an embodiment, the DUT **1026** is a system on a chip (SOC) such as a SOC made by Intel. In an embodiment, the DUT **1026** is a memory chip such as a NAND memory chip made by Intel. Other chips may be used as the DUT **1026**.

In an embodiment, the DUT **1026** is affixed to a mounting substrate **1050** with encapsulation material **1052** that leaves the backside surface **1028** exposed as bare die. The encapsulation material **1052** is contacted by an inner seal **1054** that is part of a direct fluid-contact thermal block **1001** with a die interface surface **1010**. The direct fluid-contact thermal block **1001** is depicted in simplified form compared to the direct fluid-contact thermal block **101** illustrated in FIGS. **1**, **3**, **5**, and **6**.

An inner cavity **1056** is shown between the backside surface **1028** of the DUT **1026** and the die interface surface **1010**. The inner cavity **1056** can be de-pressurized to prevent unwanted cooling fluid from exiting and fouling the structures peripheral to the DUT **1026**.

The direct fluid-contact thermal block **1001** is held in place with a package sealing block **1058** and a thermal fluid porting block **1060**. The package sealing block **1058** is configured to receive a pressurized fluid **1062** into a pressurized outer cavity **1064**. A pressure differential between the inner cavity **1056** and the pressurized outer cavity **1064** prevents unwanted cooling fluid from contacting other parts of the DUT **1026**.

The pressurized outer cavity **1064** is sealed to the package sealing block **1058** with a plurality of gaskets such as sealing block O-rings **1066** and **1068**. The direct fluid-contact thermal block **1001** is sealed to the thermal fluid porting block **1060** with a plurality of gaskets such as thermal block O-rings **1070**.

Temperature control fluid-flow direction is illustrated with the arrow **1017** to a generically depicted supply-fluid inlet **1022** and returning fluid-flow direction is illustrated with the arrow **1020** exiting a generically depicted return-fluid outlet **1024**.

The direct fluid-contact thermal block **1001** is depicted under a pressure seal **1070** from the thermal fluid porting block **1060**. Spring-loaded shoulder bolts **1072** guide the thermal fluid porting block **1060** onto the direct fluid-contact thermal block **1001** and springs **1074** allow for recoil after pressure is applied.

FIG. **10b** is a cross-section elevation of the chip-testing system depicted in FIG. **10a** after further processing according to an embodiment. The thermal fluid porting block **1060** has retracted by recoil of the springs **1074** such that the thermal fluid porting block **1060** has abutted the shoulder bolts **1072**. The inner cavity **1056** is shown to be larger between the backside surface **1028** of the DUT **1026** and the die interface surface **1010** than the illustration in FIG. **10a**.

It can also be seen that the direct fluid-contact thermal block **1001** has retracted along with the thermal fluid porting block **1060**. During the illustrated action, a negative pressure can be imposed within the inner cavity **1056**. In this method embodiment, the DUT **1026** can be moved and transported by suction after testing. The directional arrows **1090** illustrate air flow direction during pulling a low-pressure environment within the inner and outer cavities **1056** and **1064**, respectively.

FIG. **11** is a perspective elevation of a portion of a chip-testing system **1100** according to an example embodiment. A device under test **1126** is depicted with a backside surface **1128** exposed. The DUT **1126** is affixed to a mounting substrate **1150** with encapsulation material **1152** that leaves the backside surface **1128** exposed as bare die.

The encapsulation material **1152** is contacted by an inner seal **1154**. The inner seal **1154** may be referred to as a die interface **1152**. The die interface **1152** is a liquid-impermeable material that both seals the die backside surface and prevents liquid from escaping. The inner seal **1154** includes a block flange **1180**, a collapsible wall **1182**, and a device flange **1184** according to an embodiment. The device flange **1184** abuts the encapsulation material **1152** but does not touch the DUT **1126** according to an embodiment. Consequently, the DUT **1126** backside surface **1128** may be exposed entirely to temperature-control fluids without risk of fouling or physical damage to the DUT **1126**, but peripheral structures are protected from contact with the thermal-control fluid.

In an embodiment, the aspect ratio of the height of the collapsible wall **1182** to the width (height-to-width) of either of the flanges **1180** and **1184** is 1:1. In an embodiment, the aspect ratio is in a range from 1.1:1 to 2:1. As the aspect ratio increases, more downward motion of the direct fluid-contact

thermal block may be allowed to achieve a more useful spacing between the backside **1128** of the DUT **1126** and the base plane of the direct fluid-contact thermal block. Significant enough pressure may be placed on the encapsulation material **1152** that surrounds the DUT **1126** in order to simultaneously achieve more secure sealing and a more useful spacing during testing.

FIG. **12** is a bottom perspective plan of a chip-testing system **1200** according to an example embodiment. A direct fluid-contact thermal block **1201** is seen along with a microchannel array **1212** for making direct contact to a DUT. A plurality of head bolt orifices are provided, one of which is indicated with reference numeral **1214**.

An inner cavity **1256** area and a pressurized outer cavity **1264** area are separated by an inner seal **1254** and also surrounded by a sealing-block O-ring **1266**. The inner cavity **1256** can be de-pressurized to prevent unwanted cooling fluid from exiting.

Pressure control may be achieved through a plurality of pressure ports, one of which is indicated with reference numeral **1274**. The direct fluid-contact thermal block **1201** is held in place with a package sealing block and a thermal fluid porting block **1260**. Spring-loaded shoulder bolts **1272** guide the thermal fluid porting block **1260** onto the direct fluid-contact thermal block **1201**.

FIG. **13** is a top plan of a resistive heater that is embedded in a laminate layer **1300** for a fluid-contact thermal block according to an example embodiment. A laminate type **1380** is depicted with a fluid-flow array **1312** that may be near a die interface surface. It will now be understood, however, that a resistive heater may be placed interstitial to fluid-flow orifices at several laminate types.

A resistive heater **1382** is laid out between electrical terminals **1384** and **1385** and that undulates through the fluid-flow array **1312** in order to make conductive heat transfer to fluid that is passing through the microchannels. In an embodiment, the ceramic insert replaces at least one laminate type layer such as the illustrated laminate types depicted in FIG. **6a** through **6f**. Consequently, the resistive heater will undulate between the structures such as collectors, plenums, and distributors etc. depending upon the laminate type.

The resistive heater **1382** passes in the close proximity to a unit cell that includes a fluid-supply first orifice **1316** and a fluid-supply subsequent orifice **1318**, along with a single fluid-return orifice **1320**.

In an embodiment, the resistive heater **1382** is configured to cover a fraction of the fluid-flow array **1312**. For example, half of the fluid-flow array **1312** may be covered with the resistive heater **1382** by exiting the array **1312** at the point **1386** such that half of the array **1312_x** is covered by the resistive heater **1382**, and all of the array **1312_y** is covered. In this configuration the resistive heater **1382** exits array **1312** and connects to the terminal **1385** from the point **1386**. Consequently, a fraction of the array **1312** may apply resistive heat to the DUT while the balance of the array **1312** may be cooling or passive during testing. Such fractional array layout is useful to temperature control only a portion of a DUT.

FIG. **14** is a control method diagram **1400** according to several embodiments. A DUT **1402** is temperature controlled in part by circulating a cooling fluid **1404** in a feedback loop.

Temperature control of the DUT includes monitoring the inlet temperature **1410** of the temperature-control fluid as

well as the outlet temperature **1412**. The temperature of the DUT **1402** is also monitored at the die junction temperature **1414**.

In an embodiment, coolant type **1416** is water. In an embodiment, coolant type **1416** is propendiol. Other coolants may be used depending upon a given testing requirement.

A chiller **1418** is placed within the feedback loop and fluid flow is driven by a pump **1420**. In an embodiment, pump control is carried out with an H-bridge **1428**. The control method incorporates the pump **1420** in which the speed of the pump is controlled by a pulse-width-modulation control **1430** connected to the H-bridge **1428**. By controlling the speed of the pump **1420**, the thermal resistance of the direct fluid-contact thermal block is varied and consequently the die temperature may be controlled.

The flow regime is controllable with a flow filter **1422** and monitorable with a flow meter **1424**. Flow-regime control is assisted with the H-bridge **1428**, which provides the capability to both reverse the pump motor direction and apply motor braking/deceleration to quickly change the flow rate through the cold plate and thus the die temperature. Pulse width modulating the input to the pump motor allows for precise control of the pump speed for flow rate control. As the die heat flux increases and consequently the die temperature, the pump speed increases to provide additional cooling. Likewise, as the die heat flux decreases, the pump speed decreases to maintain a constant die temperature.

Another control method integrates the laminate type (e.g. laminate type **1380**, such as a ceramic plate, with the internal resistive heating traces **1382**) into the base of the direct fluid-contact thermal block, which enables modulation and dynamic control of the die.

In an embodiment, the resistive heating traces **1382** are replaced by an inline direct liquid cooling micro channel that is combined with either a resistive thin film heater or thermoelectric cooler to actively control the inlet fluid temperature set point to the direct liquid cooling micro channel. Controlling the inlet fluid temperature set point provides the capability to target the nominal temperature of the die.

Returning to FIG. **14**, a power supply **1432** is provided to drive the pump **1420** and other devices. The power supply **1432** is also connected to a controller that may be a proportional-integral-derivative (PID) controller **1426** that can respond to test conditions. Other control methods may include servo (user-directed) control. In an embodiment, proportional control is used. In an embodiment, integral control is used. In an embodiment, derivative control is used. In an embodiment, a combination of control methods is used. The controller **1426** may also operate in heating mode with the use of internal resistive heating traces such as set forth in this disclosure.

Although a device under test may refer to a processor chip, a processor chip or a memory chip may be mentioned in the same sentence, but it should not be construed that they are equivalent structures. Reference throughout this disclosure to "one embodiment" or "an embodiment" means that a particular feature, structure, or characteristic described in connection with the embodiment is included in at least one embodiment of the present invention. The appearance of the phrases "in one embodiment" or "in an embodiment" in various places throughout this disclosure are not necessarily all referring to the same embodiment. Furthermore, the particular features, structures, or characteristics may be combined in any suitable manner in one or more embodiments.

Terms such as "upper" and "lower" "above" and "below" may be understood by reference to the illustrated X-Z coordinates, and terms such as "adjacent" may be understood by reference to X-Y coordinates or to non-Z coordinates.

The Abstract is provided to comply with 37 C.F.R. §1.72(b) requiring an abstract that will allow the reader to quickly ascertain the nature and gist of the technical disclosure. It is submitted with the understanding that it will not be used to interpret or limit the scope or meaning of the claims.

In the foregoing Detailed Description, various features are grouped together in a single embodiment for the purpose of streamlining the disclosure. This method of disclosure is not to be interpreted as reflecting an intention that the claimed embodiments of the invention require more features than are expressly recited in each claim. Rather, as the following claims reflect, inventive subject matter lies in less than all features of a single disclosed embodiment. Thus the following claims are hereby incorporated into the Detailed Description, with each claim standing on its own as a separate preferred embodiment.

It will be readily understood to those skilled in the art that various other changes in the details, material, and arrangements of the parts and method stages which have been described and illustrated in order to explain the nature of this invention may be made without departing from the principles and scope of the invention as expressed in the subjoined claims.

What is claimed is:

1. An apparatus including a direct fluid-contact thermal block to temperature-control a semiconductive device, comprising:

- a first laminate type including a plurality of unit block perimeters;
- a base plane second laminate type, wherein the base plane second laminate type includes at least one heat-transfer fluid unit cell, the at least one heat-transfer fluid unit cell including:
 - a fluid supply structure including a supply-orifice cross-sectional area; and
 - a fluid return structure including a return-orifice cross-sectional area, wherein the supply-orifice cross-sectional area is greater than the return-orifice cross-sectional area;
- a third laminate type including fluid-supply distributors coupled to the fluid supply structure, and fluid-return collectors coupled to the fluid return structure;
- a fourth laminate type including fluid supply- and return routers, respectively, that couple to the respective fluid supply- and return distributors and collectors;
- a fifth laminate type includes fluid supply- and return plenums, respectively, that couple to the respective fluid supply- and return routers; and
- a sixth laminate type including a top plane of the direct fluid-contact thermal block and including supply-fluid inlets and return-fluid outlets, respectively, that are coupled to the respective fluid supply- and return plenums; wherein

the first laminate type is 5 mils (thousandths of an inch) thick and is a single layer;

the base plane second laminate type includes a fluid-flow array of 120 unit cells defined by a 24 unit-cell dimension along an X-axis and a five unit-cell dimension along a Y-axis, and wherein the base plane second laminate type is 5 mils thick and includes a total of 4 layers;

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the third laminate type is 10 mils thick and includes a total of nine layers;
 the fourth laminate type is 10 mils thick and includes a total of nine layers;
 the fifth laminate type is 10 mils thick and includes a total of five layers; and
 the sixth laminate type is 10 mils thick and includes a total of two layers.

2. The apparatus of claim 1, wherein the laminate types comprise stainless steel.

3. The apparatus of claim 1, wherein the laminate types comprise ceramic material.

4. The apparatus of claim 1, wherein the laminate types comprise polymeric material.

5. The apparatus of claim 1, wherein at least one of the laminate types includes resistive heating traces coupled thereto.

6. The apparatus of claim 1, further comprising a chiller.

7. An apparatus including a direct fluid-contact thermal block to temperature-control a semiconductive device, comprising:

a first laminate type including a plurality of unit block perimeters;

a second laminate type includes a fluid supply structure comprising a plurality of fluid supply-orifices and a fluid return structure comprising a plurality of fluid return-orifices, the fluid supply structure and the fluid return structure configured to include a greater number of fluid supply-orifices than fluid return-orifices;

a third laminate type including fluid-supply distributors coupled to the fluid supply structure, and fluid-return collectors coupled to the fluid return structure;

a fourth laminate type including fluid supply- and return routers, respectively, that couple to the respective fluid supply- and return distributors and collectors;

a fifth laminate type includes fluid supply- and return plenums, respectively, that couple to the respective fluid supply- and return routers; and

a sixth laminate type including an upper layer of the direct fluid-contact thermal contact block and including supply-fluid inlets and return-fluid outlets, respectively, that are coupled to the respective fluid supply- and return plenums;

wherein the first laminate type is 5 mils thick and is a single layer;

wherein the second laminate type is 5 mils thick and includes a total of four layers;

wherein the third laminate type is 10 mils thick and includes a total of nine layers;

wherein the fourth laminate type is 10 mils thick and includes a total of nine layers;

wherein the fifth laminate type is 10 mils thick and includes a total of five layers; and

wherein the sixth laminate type is 10 mils thick and includes a total of two layers.

8. The apparatus of claim 7, wherein the fluid supply structure includes twice as many fluid supply-orifices as fluid return-orifices.

9. The apparatus of claim 7, wherein the second laminate type includes a planar surface including a plurality of heat-transfer fluid unit cells, the fluid supply-orifices and the fluid return-orifices positioned in the plurality of heat-

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transfer fluid unit cells, the plurality of heat-transfer fluid unit cells each including two supply orifices and a single return orifice therein.

10. The apparatus of claim 9, wherein the second laminate type includes a fluid-flow array of 120 unit cells defined by a 24 unit-cell dimension along an X-axis and a five unit-cell dimension along a Y-axis.

11. The apparatus of claim 7, wherein the laminate types comprise stainless steel.

12. The apparatus of claim 7, wherein the laminate types comprise ceramic material.

13. The apparatus of claim 7, wherein the laminate types comprise polymeric material.

14. The apparatus of claim 7, wherein at least one of the laminate types includes resistive heating traces coupled thereto.

15. An apparatus including a plurality of layers laminated together to form a direct fluid-contact thermal block configured to temperature-control a semiconductive device, comprising:

a first laminate type including a first surface;

a second laminate type including fluid-supply orifices and fluid-return orifices arranged in a fluid-flow array of unit cells, the unit cells each including two fluid-supply orifices and a single fluid-return orifice positioned between the two fluid-supply orifices;

a third laminate type including fluid-supply distributors in communication with the fluid-supply orifices, and fluid-return distributors in communication with the fluid-return orifices;

a fourth laminate type including fluid-supply routers in communication with the fluid-supply distributors, and fluid-return routers in communication with the fluid-return distributors;

a fifth laminate type including fluid-supply plenums in communication with the fluid-supply routers, and fluid-return plenums in communication with the fluid-return routers; and

a sixth laminate type including supply-fluid inlets in communication with the fluid-supply plenums, and return-fluid outlets in communication with the fluid-return plenums;

wherein the first laminate type is 5 mils thick and is a single layer;

wherein the second laminate type is 5 mils thick and includes a total of four layers;

wherein the third laminate type is 10 mils thick and includes a total of nine layers;

wherein the fourth laminate type is 10 mils thick and includes a total of nine layers;

wherein the fifth laminate type is 10 mils thick and includes a total of five layers; and

wherein the sixth laminate type is 10 mils thick and includes a total of two layers.

16. The apparatus of claim 15, wherein the laminate types comprise stainless steel.

17. The apparatus of claim 15, wherein the laminate types comprise ceramic material.

18. The apparatus of claim 15, wherein the laminate types comprise polymeric material.

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